

## FDC6561AN

### Dual N-Channel Logic Level PowerTrench™ MOSFET

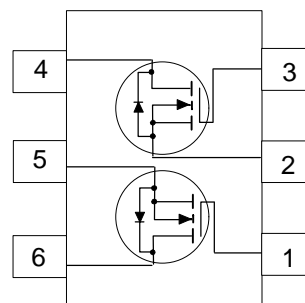
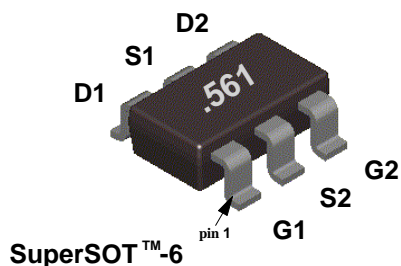
#### General Description

These N-Channel Logic Level MOSFETs are produced using Fairchild Semiconductor's advanced PowerTrench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for all applications where small size is desirable but especially low cost DC/DC conversion in battery powered systems.

#### Features

- 2.5 A, 30 V.  $R_{DS(ON)} = 0.095 \Omega @ V_{GS} = 10 \text{ V}$   
 $R_{DS(ON)} = 0.145 \Omega @ V_{GS} = 4.5 \text{ V}$
- Very fast switching.
- Low gate charge (2.1nC typical).
- SuperSOT™-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



#### Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$  unless otherwise note

Symbol	Parameter	Ratings	Units	
$V_{DS}$	Drain-Source Voltage	30	V	
$V_{GS}$	Gate-Source Voltage - Continuous	$\pm 20$	V	
$I_D$	Drain Current - Continuous	2.5	A	
	- Pulsed	10		
$P_D$	Maximum Power Dissipation	(Note 1a)	0.96	W
		(Note 1b)	0.9	
		(Note 1c)	0.7	
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 150	$^\circ\text{C}$	

#### THERMAL CHARACTERISTICS

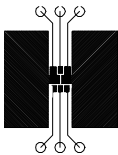
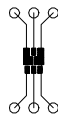
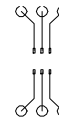
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	60	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
<b>OFF CHARACTERISTICS</b>							
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	30			V	
$\Delta V_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		23.6		$\text{mV}/^\circ\text{C}$	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$	
		$T_J = 55^\circ\text{C}$			10	$\mu\text{A}$	
$I_{GSSF}$	Gate - Body Leakage, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA	
$I_{GSSR}$	Gate - Body Leakage, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA	
<b>ON CHARACTERISTICS</b> (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	1	1.8	3	V	
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp. Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-4		$\text{mV}/^\circ\text{C}$	
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 2.5\text{ A}$		0.082	0.095	$\Omega$	
		$T_J = 125^\circ\text{C}$		0.122	0.152		
		$V_{GS} = 4.5\text{ V}, I_D = 2.0\text{ A}$		0.113	0.145		
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	10			A	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 2.5\text{ A}$		5		S	
<b>DYNAMIC CHARACTERISTICS</b>							
$C_{iss}$	Input Capacitance	$V_{DS} = 15\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		220		pF	
$C_{oss}$	Output Capacitance				50		pF
$C_{rss}$	Reverse Transfer Capacitance				25		pF
<b>SWITCHING CHARACTERISTICS</b> (Note 2)							
$t_{D(on)}$	Turn - On Delay Time	$V_{DD} = 5\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\ \Omega$		6	12	ns	
$t_r$	Turn - On Rise Time			10	18		
$t_{D(off)}$	Turn - Off Delay Time			12	22		
$t_f$	Turn - Off Fall Time			2	6		
$Q_g$	Total Gate Charge	$V_{DS} = 15\text{ V}, I_D = 2.5\text{ A}$		2.3	3.2	nC	
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 5\text{ V}$		0.7	1		
$Q_{gd}$	Gate-Drain Charge			0.9	1.3		
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
$I_S$	Continuous Source Diode Current				0.75	A	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.75\text{ A}$ (Note 2)		0.78	1.2	V	

Notes:

 1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

 2. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

 a.  $130^\circ\text{C}/\text{W}$  on a  $0.125\text{ in}^2$  pad of 2oz copper.

 b.  $140^\circ\text{C}/\text{W}$  on a  $0.005\text{ in}^2$  pad of 2oz copper.

 c.  $180^\circ\text{C}/\text{W}$  on a minimum pad.

## Typical Electrical Characteristics

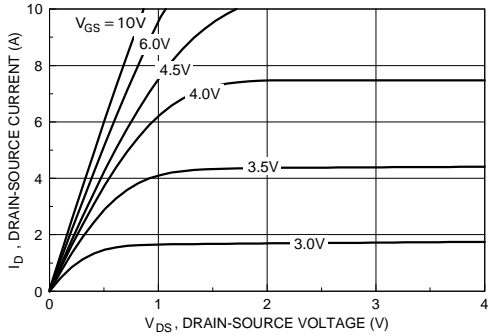


Figure 1. On-Region Characteristics.

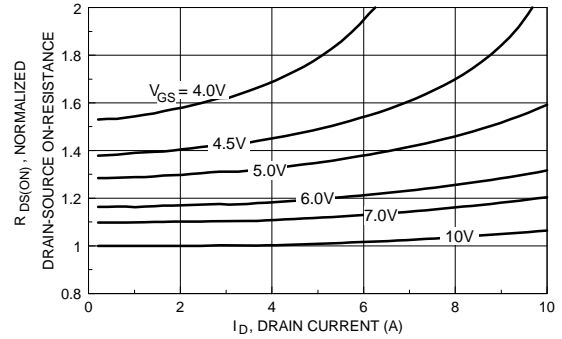


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

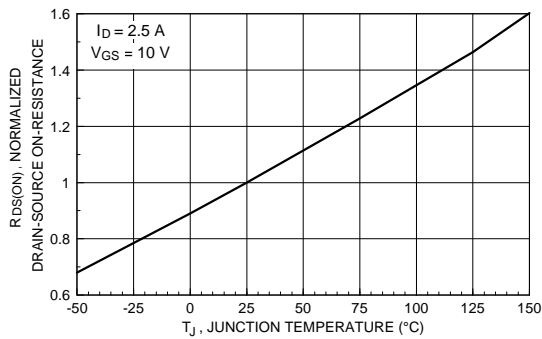


Figure 3. On-Resistance Variation with Temperature.

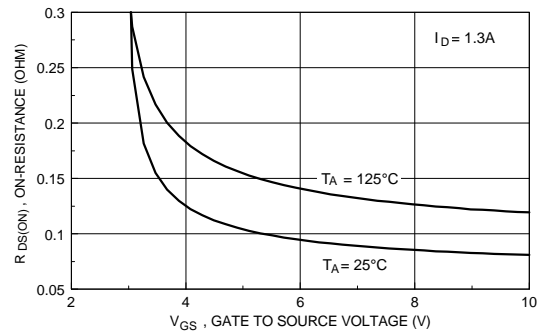


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

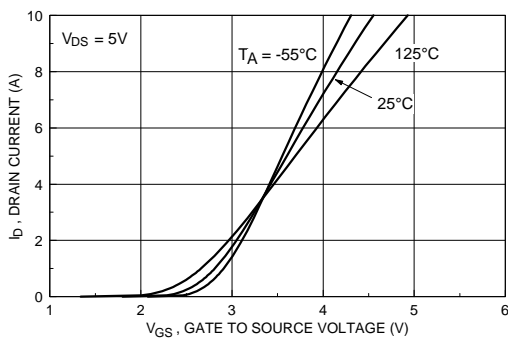


Figure 5. Transfer Characteristics.

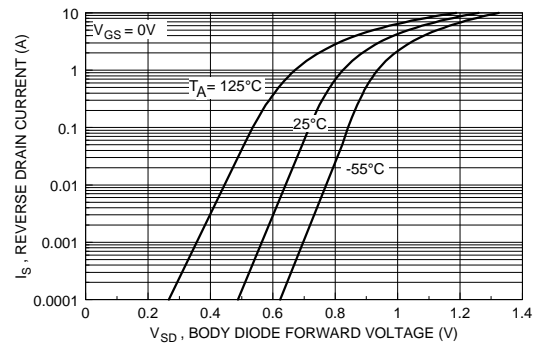


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Electrical Characteristics (continued)

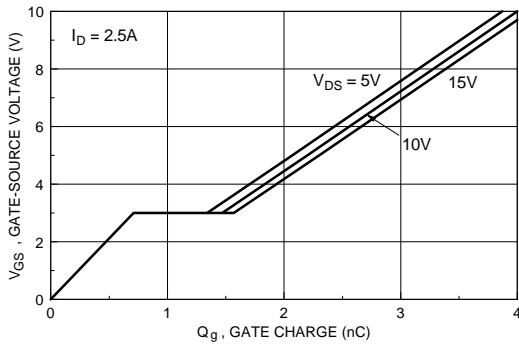


Figure 7. Gate Charge Characteristics.

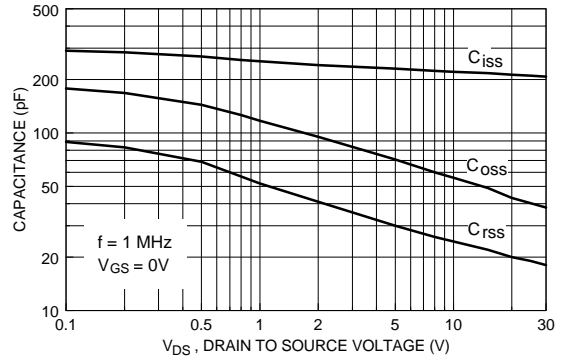


Figure 8. Capacitance Characteristics.

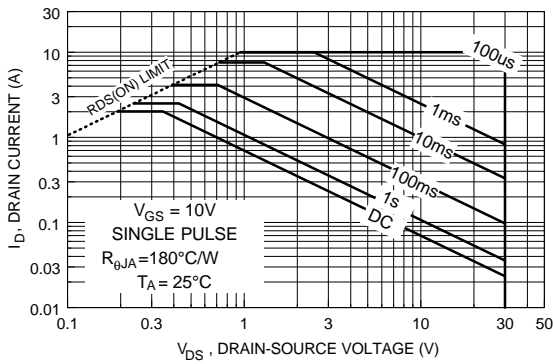


Figure 9. Maximum Safe Operating Area.

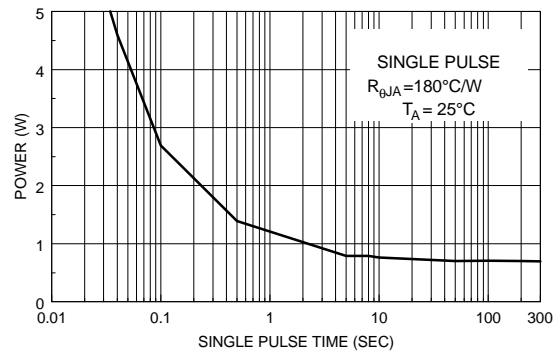


Figure 10. Single Pulse Maximum Power Dissipation.

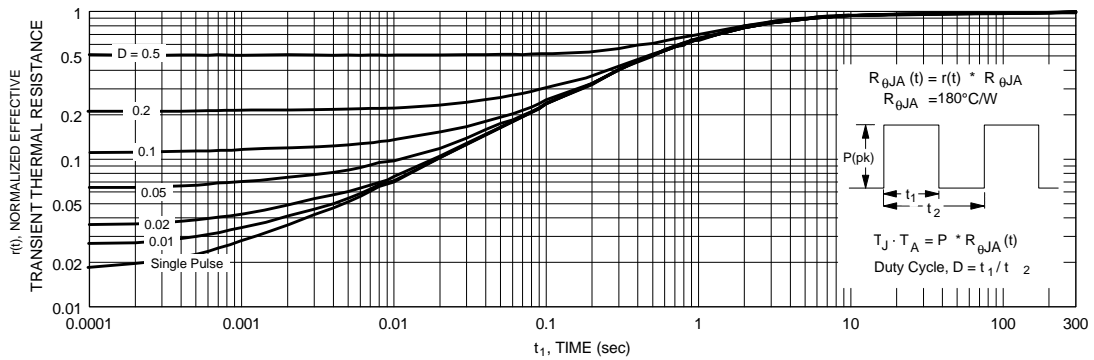


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
Transient thermal response will change depending on the circuit board design.

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